

II. Specification

In response to the Examiner's request to check and correct errors in the specification, the undersigned is reviewing the specification and will submit amendments to the specification to correct grammatical errors therein as soon as the review is finished.

III. §112

The Examiner also rejects Claim 1 under 35 USC §112 as containing subject matter which was not described in the specification in such a way as to reasonably convey to one skilled in the relevant art that the inventor at the time the application was filed had possession of the claimed invention. In particular, the Examiner refers to Fig. 28. This rejection is respectfully traversed as Applicants wish to draw the Examiner's attention to Fig. 1 and pages 18-19 of the specification as showing support for Claim 1.

Further, in order to resolve any confusion, Applicants are amending Claim 1 to recite that the first impurity region of the n-channel TFT is disposed so as to partially overlap with a portion of the second conductive layer which is in contact with said gate insulating film; and that the third impurity region of the p-channel TFT is disposed so as to partially overlap with another portion of the second conductive layer which is in contact with the gate insulating film. This is clearly supported by Figure 1 and page 18, ln. 14 to page 19, ln. 20.

Accordingly, it is requested that this rejection be withdrawn.

IV. Prior Art Rejection

The Examiner also rejects Claim 1 under 35 USC §103 as being unpatentable over Goser. This rejection is respectfully traversed.

As explained above, Claim 1 recites that first impurity region of the n-channel TFT is disposed so as to partially overlap with a portion of the second conductive layer which is in contact with said gate insulating film; and that the third impurity region of the p-channel TFT is disposed so as to partially overlap with another portion of the second conductive layer which is in contact with the gate insulating film.

In contrast, in Fig. 6 of Goser, 421 and 521, which were cited by the Examiner in the office action, completely overlap the gate electrode. Further, Goser also does not appear to disclose a second conductive layer of the gate electrode in contact with a first conductive layer and a gate insulating film, as required by Claim 1.

Accordingly, the structure of Claim 1 is clearly distinguishable from that disclosed in the cited reference and is patentable thereover.

V. Further Amendments

Applicants have further amended Claim 1 to recite the limitations of a ferroelectric liquid crystal (which is shown in Fig. 39 and Embodiment 21) and added new Claims 1-13 directed to this feature and also new Claims 14-26 directed to a goggle-type display device (shown in Fig. 15D and Embodiment 14). Further, Applicants are herein filing an Information Disclosure Statement citing a related application serial no. 09/432,662 having a same priority date as the subject application. Applicants submit that the above limitations in the present claim and new claim of the subject application distinguish over the 09/432,662 application.

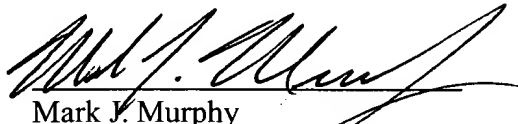
VI. Conclusion

Accordingly, for the above-stated reasons, the claims of the present application are not disclosed or suggested by the cited references and are patentable thereover. Therefore, it is requested that the claims now be allowed.

Favorable reconsideration is earnestly solicited.

Respectfully submitted,

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